

1 Amendments to the Claims:

2 This listing of claims will replace all prior versions, and  
3 listings, of claims in the application:

4 (Original) (Currently Amended) (New) (Canceled)

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6 Listing of Claims:

7 1. (Currently Amended) A MOSFET for receiving an applied voltage  
8 and a gate voltage, the MOSFET comprising,  
9 a first terminal in a semiconductor material,  
10 a gate terminal receiving the gate voltage, the gate being  
11 disposed over a channel of the semiconductor material, the gate and  
12 channel being curved defined by a gate curvature, the gate being  
13 insulated from the semiconductor material, the channel having two  
14 channel ends, the two channel ends being nonparallel nonaligned  
15 channel ends, the curve of the gate and the channel are  
16 noninflecting,  
17 an insulator disposed between the gate and the semiconductor  
18 material, and  
19 a second terminal in the semiconductor material, the applied  
20 voltage extends between the first terminal and the second terminal,  
21 the gate voltage serving to control conduction between the first  
22 terminal and the second terminal in the presence of the gate  
23 voltage, the applied voltage serving to establish a diverging  
24 electric field extending from the first terminal through the  
25 channel to the second terminal, the MOSFET being a triode MOSFET.

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1 2. (Original) The MOSFET of claim 1 wherein,

2 the gate curvature is defined by a radius extending from a point  
3 inside the first terminal.

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5 3. (Original) The MOSFET of claim 1 wherein,

6 the gate curvature of the gate is defined by a radius extending  
7 from a point inside the first terminal, the gate curvature is less  
8 than a semicircle.

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10 4. (Original) The MOSFET of claim 1 wherein,

11 the gate curvature is defined by a radius extending from a point  
12 inside the first terminal, the gate curvature is a quarter circle.

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14 5. (Original) The MOSFET of claim 1 wherein,

15 the gate curvature is defined by a radius extending from a point  
16 inside the first terminal, the gate curvature is an eighth circle.

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1 6. (Currently Amended) A MOSFET for receiving an applied voltage  
2 and a gate voltage, the MOSFET comprising,  
3 a source terminal in n-type silicon,  
4 a gate terminal receiving the gate voltage, the gate being  
5 disposed over a channel of the n-type silicon, the gate being  
6 insulated from the n-type silicon, the channel having two channel  
7 ends, the two channel ends being nonparallel nonaligned channel  
8 ends, the curve of the gate and the channel are noninflecting,  
9 an insulator disposed between the gate and the n-type silicon,  
10 and  
11 a drain terminal in the n-type silicon, the applied voltage  
12 extends between the source terminal and the drain terminal, the  
13 gate voltage serving to control conduction between the source  
14 terminal and the drain terminal in the presence of the gate  
15 voltage, the applied voltage serving to establish a diverging  
16 electric field extending from the source terminal through the  
17 channel to the drain terminal, the MOSFET being a triode MOSFET.

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19 7. (Original) The MOSFET of claim 6 further comprising,  
20 a silicon substrate,  
21 a p-type well disposed within the substrate, the source terminal  
22 and drain terminal and channel being disposed in the p-type well.

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24 8. (Original) The MOSFET of claim 6 wherein,  
25 the curve of the gate is defined by a radius extending from a  
26 point inside the source terminal.

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1 9. (Original) The MOSFET of claim 6 wherein,

2 the gate curvature is defined by a radius extending from a point  
3 inside the source terminal, the gate curvature is less than a  
4 semicircle.

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6 10. (Original) The MOSFET of claim 6 wherein,

7 the gate curvature is defined by a radius extending from a point  
8 inside the source terminal, the gate curvature is a quarter circle.

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11 11. (Original) The MOSFET of claim 6 further comprising,  
12 a p-type silicon well.

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15 12. (Original) The MOSFET of claim 6 further comprising,

16 a source connector,

17 a source contact in the source connector for connecting the  
18 source connector to the source terminal,

19 a drain connector, and

20 a drain contact in the drain connector for connecting the drain  
21 connector to the drain terminal, the applied voltage being applied  
22 between the source connector and the drain connector.

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1 13. (Original) The MOSFET of claim 6 further comprising,  
2 a source connector,  
3 a source contact in the source connector for connecting the  
4 source connector to the source terminal,  
5 a drain connector, and  
6 a plurality of drain contacts in the drain connector for  
7 connecting the drain connector to the drain terminal, the applied  
8 voltage being applied between the source connector and the drain  
9 connector.

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14 14. (Original) The MOSFET of claim 6 further comprising,  
15 a p-type silicon well,  
16 a source connector,  
17 a source contact in the source connector for connecting the  
18 source connector to the source terminal,  
19 a drain connector, and  
20 a drain contact in the drain connector for connecting the drain  
21 connector to the drain terminal, the applied voltage being applied  
22 between the source connector and the drain connector.

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2 15. (Original) The MOSFET of claim 6 further comprising,  
3 a p-type silicon well,  
4 a source connector,  
5 a source contact in the source connector for connecting the  
6 source connector to the source terminal,  
7 a drain connector, and  
8 a plurality of drain contacts in the drain connector for  
9 connecting the drain connector to the drain terminal, the applied  
10 voltage being applied between the source connector and the drain  
11 connector.

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13 16. (New) The MOSFET of claim 1 wherein,  
14 the gate curvature of the gate is defined by a radius extending  
15 from a point inside the first terminal, the gate curvature is less  
16 than or equal to a quartercircle.

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18 17. (New) The MOSFET of claim 6 wherein,  
19 the gate curvature of the gate is defined by a radius extending  
20 from a point inside the first terminal, the gate curvature is less  
21 than or equal to a quartercircle.

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